

JIEJIE MICROELECTRONICS CO., LTD.

Average gate power dissipation ($T_j=150$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	4	kV

ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V$ $R_L=33\Omega$	- -	MAX.	50	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=150$ $R_L=3.3k\Omega$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	80	mA
				100	
I_H	$I_T=500mA$		MAX.	60	mA
dV/dt	$V_D=400V$ Gate Open $T_j=150$		MIN.	2000	V/ μs
$(dI/dt)_c$	$(dV/dt)_c=20V/\mu s$, $T_j=150$		MIN.	25	A/ms
t_{on}	$I_G=80mA$ $I_A=400mA$ $I_R=40mA$ $T_j=25$		TYP.	12	μs
t_{off}				80	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=22.5A$ $t_p=380\mu s$	$T_j=25$	1.4	V
V_{TO}	Threshold voltage	$T_j=150$	0.75	V
R_D	Dynamic resistance	$T_j=150$	27	m Ω
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25$	5	μA
I_{RRM}		$T_j=150$	1.5	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	2.4	/W
$R_{th(j-a)}$	junction to ambient (AC)	60	/W

ORDERING INFORMATION

T	16	50	H	-6	F
Triacs	$I_T(RMS):16A$				F:TO-220F(Ins)
	$50:I_{GT1-3} 0.50mA$			$6:V_{DRM} / V_{RRM} 1600V$	
			High junction temperature		

MARKING

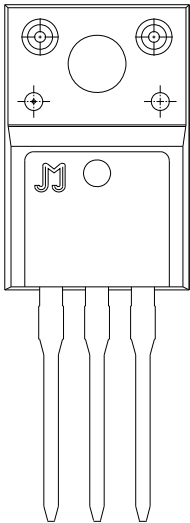
	Year Month Production Code
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FIG.1: Maximum power dissipation versus RMS on-state current

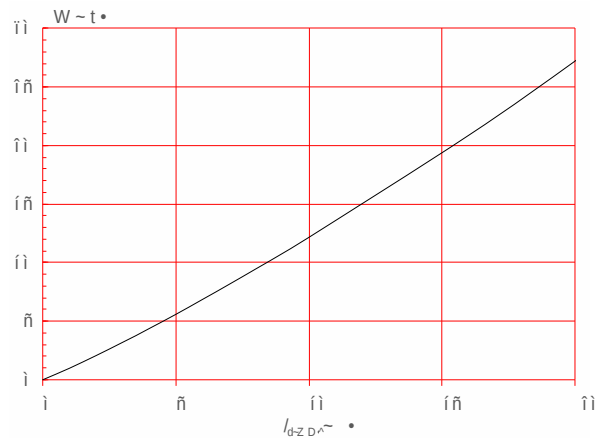


FIG.3: Surge peak on-state current versus number of cycles

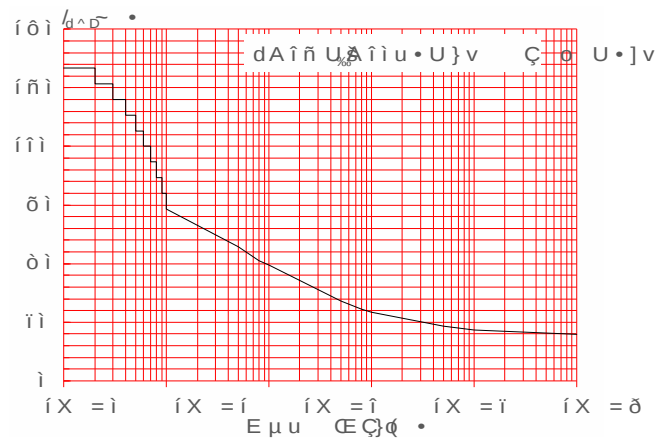


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t ($dI/dt < 100\text{A}/\mu\text{s}$)

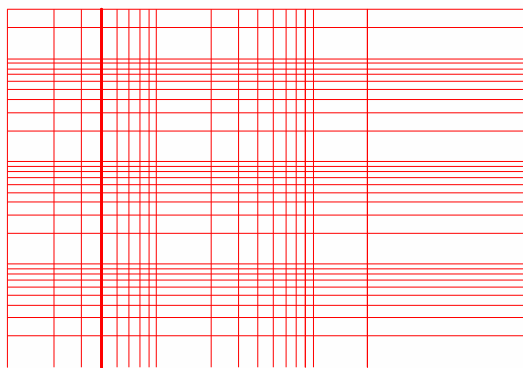


FIG.2: RMS on-state current versus case temperature

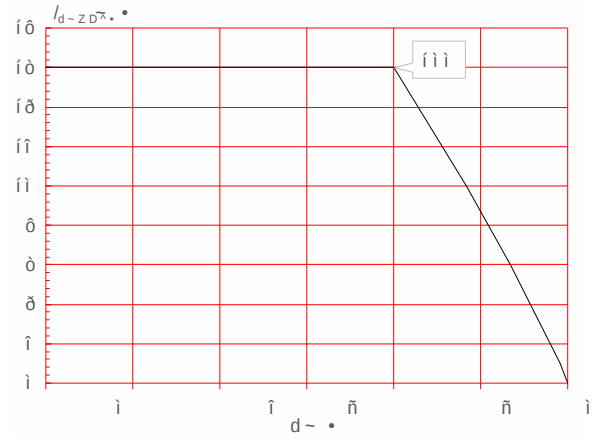


FIG.4: On-state characteristics

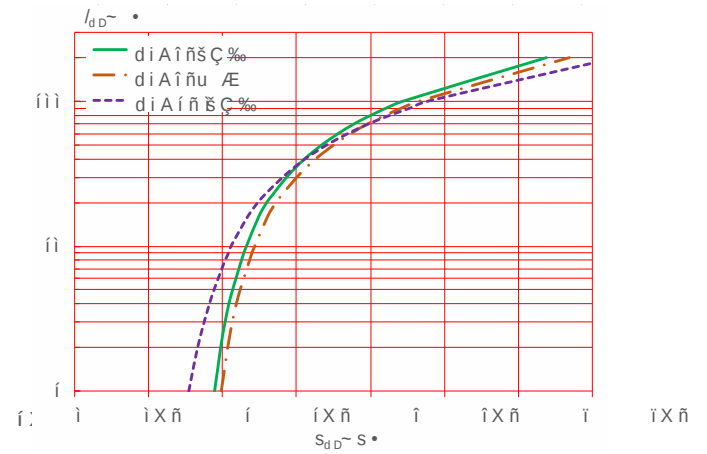
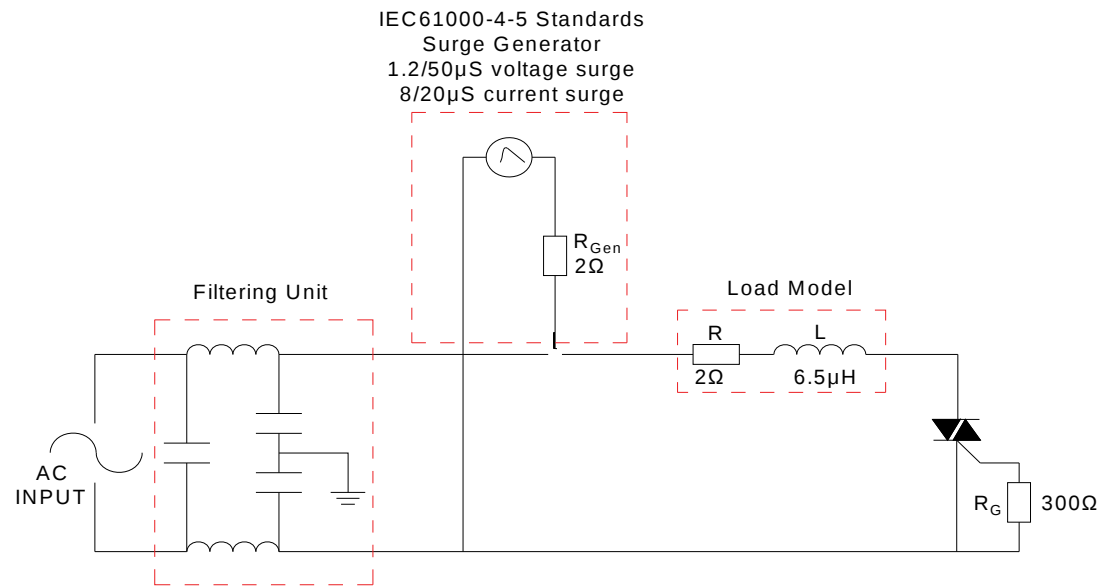


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

FIG.7 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards



ORDERING INFORMATION

Order code	Voltage V _{DRM} /V _{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery
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PACKAGE MECHANICAL DATA



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